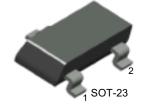


BC856/857/858/859/860

Switching and Amplifier Applications

- Suitable for automatic insertion in thick and thin-film circuits
- Low Noise: BC859, BC860
- Complement to BC846 ... BC850



1. Base 2. Emitter 3. Collector

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings Ta=25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|------------------|---------------------------|-----------|-------|
| V _{CBO} | Collector-Base Voltage | | |
| | : BC856 | -80 | V |
| | : BC857/860 | -50 | V |
| | : BC858/859 | -30 | V |
| V _{CEO} | Collector-Emitter Voltage | | |
| | : BC856 | -65 | V |
| | : BC857/860 | -45 | V |
| | : BC858/859 | -30 | V |
| V _{EBO} | Emitter-Base Voltage | -5 | V |
| I _C | Collector Current (DC) | -100 | mA |
| P _C | Collector Dissipation | 310 | mW |
| T _J | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | -65 ~ 150 | °C |

Electrical Characteristics T_a=25°C unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|-----------------------|---|---|------|--------------|--------------|----------|
| I _{CBO} | Collector Cut-off Current | V _{CB} = -30V, I _E =0 | | | -15 | nA |
| h _{FE} | DC Current Gain | V _{CE} = -5V, I _C = -2mA 110 | | | 800 | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | I _C = -10mA, I _B = -0.5mA I _C = -100mA, I _B = -5mA | | -90 -250 | -300 -650 | mV mV |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | I _C = -10mA, I _B = -0.5mA I _C = -100mA, I _B = -5mA | | -700 -900 | | mV mV |
| V _{BE} (on) | Base-Emitter On Voltage | V_{CE} = -5V, I_{C} = -2mA V_{CE} = -5V, I_{C} = -10mA | -600 | -660 | -750 -800 | mV mV |
| f _T | Current Gain Bandwidth Product | V _{CE} = -5V, I _C = -10mA f=100MHz | | 150 | | MHz |
| C _{ob} | Output Capacitance | V _{CB} = -10V, I _E =0, f=1MHz | | | 6 | pF |
| NF | Noise Figure : BC856/857/858 : BC859/860 | V_{CE} = -5V, I_{C} = -200μA f=1KHz, R_{G} =2K Ω | | 2 1 | 10 4 | dB dB |
| | : BC859 : BC860 | V _{CE} = -5V, I _C = -200μA R _G =2KΩ, f=30~15000Hz | | 1.2 1.2 | 4 2 | dB dB |

h_{FE} Classification

| Classification | А | В | С | |
|-----------------|-----------|-----------|-----------|--|
| h _{FE} | 110 ~ 220 | 200 ~ 450 | 420 ~ 800 | |

Marking Code

| Туре | 856A | 856B | 856C | 857A | 857B | 857C | 858A | 858B | 858C |
|------|------|------|------|------|------|------|------|------|------|
| Mark | 9AA | 9AB | 9AC | 9BA | 9BB | 9BC | 9CA | 9CB | 9CC |
| Туре | 859A | 859B | 859C | 860A | 860B | 860C | • | | |
| Mark | 9DA | 9DB | 9DC | 9EA | 9EB | 9EC | • | | |

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Typical Characteristics

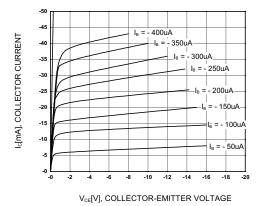


Figure 1. Static Characteristic

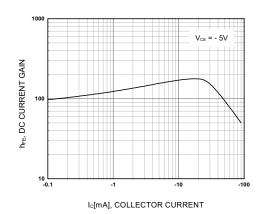


Figure 2. DC current Gain

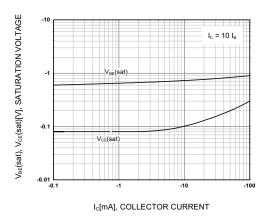


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

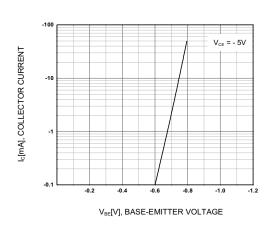


Figure 4. Base-Emitter On Voltage

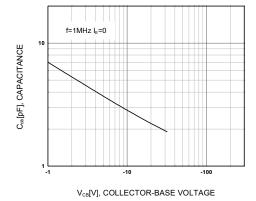


Figure 5. Collector Output Capacitance

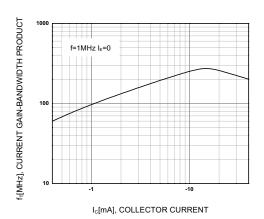
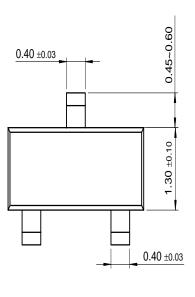


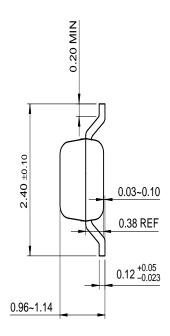
Figure 6. Current Gain Bandwidth Product

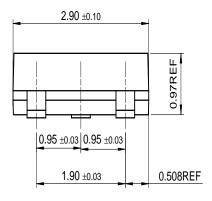
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Package Demensions

SOT-23







Dimensions in Millimeters

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